

科目：421 電子學  
系組：電機系電子組

(本試題共 / 頁, 第 / 頁)

考生注意：1. 依次序作答，只要標明題號，不必抄題。  
2. 答案必須寫在答案卷上，否則不予計分。  
3. 試題隨卷繳回。

(25%) 1. For Fig. 1, please prove that

$$I_{\text{bias}} = (V_T/R) \ln(I_{\text{bias}}/I_s)$$

(for the bipolar transistor,  $I_C = I_s e^{V_{BE}/V_T}$ )

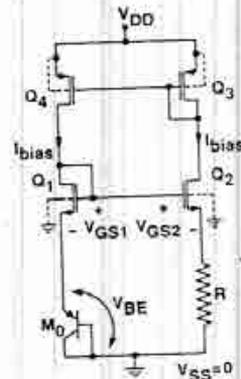


Fig. 1

(25%) 2. Please draw the small-signal equivalent circuit of the circuit shown in Fig. 2. Then derive its output resistance,  $r_{\text{out}}$ .

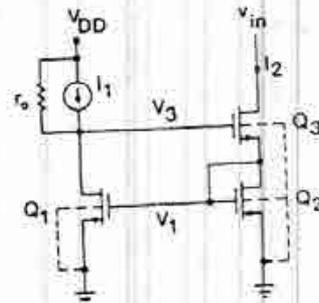


Fig. 2

(25%) 3. For the circuit shown in Fig. 3, please draw its small-signal equivalent circuit, and derive its differential-mode gain and common-mode gain.

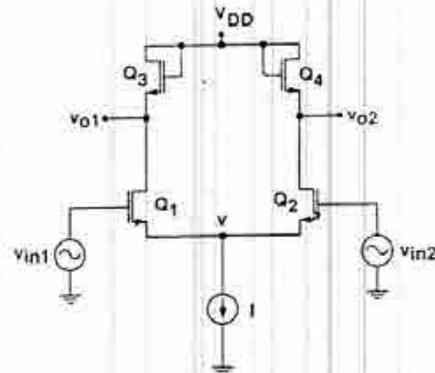


Fig. 3

(25%) 4. Please explain the following terms (no more than 100 words for each term)

- (a) AFM      (b) Body Effect      (c) CVD      (d) Electromigration  
(f) Fermi Level      (g) Short Channel Effect      (h) OLED      (i) Tunneling Effect